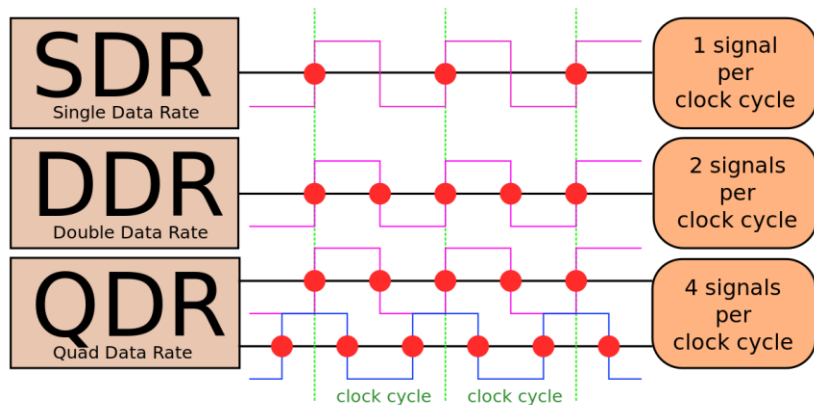


DDR SDRAM

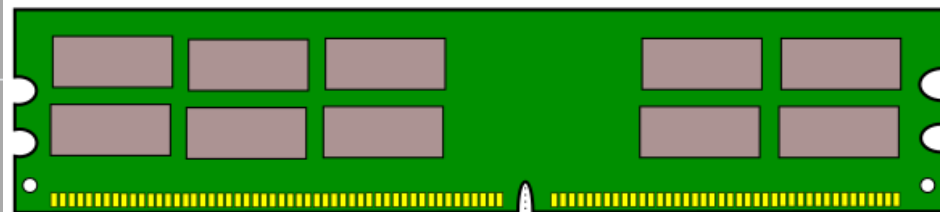
- Not backward compatible
- Low frequency =>
• reduced signal integrity requirements.
- Column x Row x Bank x Rank
• = DIMM
- 8chips x 8bit
• = 64bits (module)



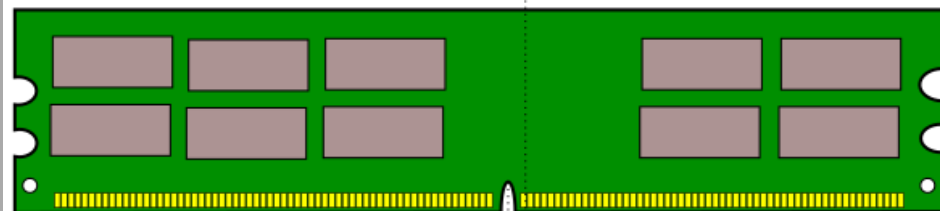
Joint Electron Device
Engineering Council

Developer	Samsung ^{[1][2][3]} Micron Hynix JEDEC
Type	<u>Synchronous</u> <u>dynamic random-</u> <u>access memory</u>
Generations	<u>DDR2</u> <u>DDR3</u> <u>DDR4</u> <u>DDR5</u>
Release date	DDR: 1998 DDR2: 2003 DDR3: 2007 DDR4: 2014 DDR5: 2020
Specifications	
Voltage	DDR: 2.5/2.6 DDR2: 1.8 DDR3: 1.5/1.35 DDR4: 1.2/1.05

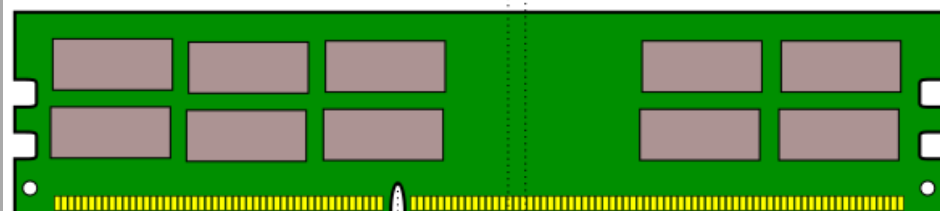
DDR



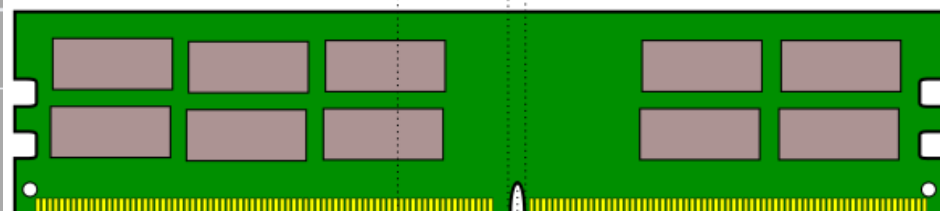
DDR 2



DDR 3



DDR 4

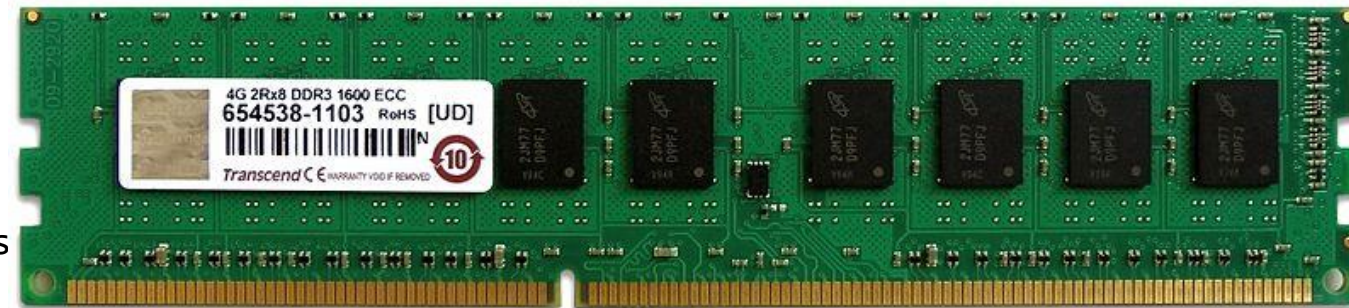


DDR3 SDRAM

- Upto 16GB, 1GB/chip, 1.5V (2005)
- CL-RCD-RP: col. delay, row delay, prech. delay
- BW: mem CK x 4 bus mult. X 2 DDR x 64b
- eXtended Memory Profile (XMP, 2007)
- DDR3L: 1.35V (2010), DDR3U: 1.25V (2011)
- DDR4-800: 100MHz mem CK x 4 = 400MHz IO CK
- 400MHz x 2 DDR x 64b = 6.4 GB/s (5-5-5)
- DDR4-2133: 266MHz mem CK x 4 = 1066MHz IO CK
- 1066MHz x 2 DDR x 64b = 17 GB/s (11-11-11)
- Hynix 16GB: (16 x 1GB) 2133MHz x 64b = 17 GB/s



16GB DDR3 SO-DIMM, 1600 MT/s, 1.35/1.5V



Transcend 4GB ECC DDR3 DRAM, 1600 MT/s (2013)

DDR4 SDRAM

- Upto 64GB, 1.2V, 40-16nm (2011)
- Power: refresh strategies, data bus inv.
- Row hammer: large capacitors, ASLR (addr. rnd.)
- DIMM: 288 pins, 0.85mm spacink
- SO-DIMM: 260 pins, 0.5mm spacing (skylake)
- DDR4-1600: $200\text{MHz mem CK} \times 4 = 800\text{MHz IO CK}$
- $800\text{MHz} \times 2 \text{ DDR} \times 64\text{b} = 12.8 \text{ GB/s (10-10-10)}$
- DDR4-3200: $400\text{MHz mem CK} \times 4 = 1600\text{MHz IO CK}$
- $1600\text{MHz} \times 2 \text{ DDR} \times 64\text{b} = 25.6 \text{ GB/s (20-20-20)}$
- Hynix 16GB: $(16 \times 1\text{GB}) 2133\text{MHz} \times 64\text{b} = 17 \text{ GB/s}$



GOOD RAM 16GB DDR4 DRAM, 2133 MT/s, 1.2V



Samsung 2GB ECC DDR4 DRAM, 2133 MT/s, 1.2V (2011)

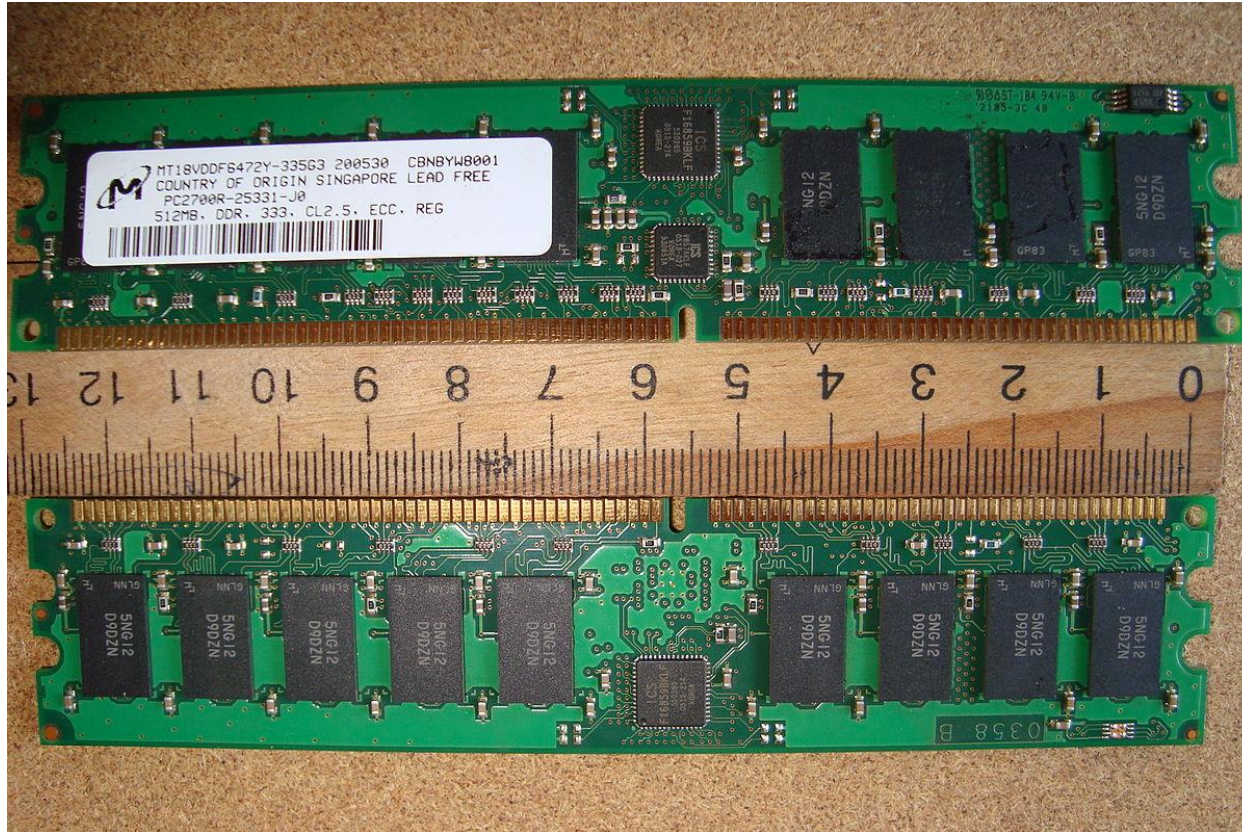
Registered Memory (RDIMM)



Two 8 GB DDR4-2133 ECC 1.2 V RDIMMs

- For high-density chips (36)
 - +1 cycle latency
 - Normally features ECC
 - Costlier, used in servers
 - Motherboard must support
-
- RDIMM: +address, +command
 - LRDIMM: +data (+capacity)

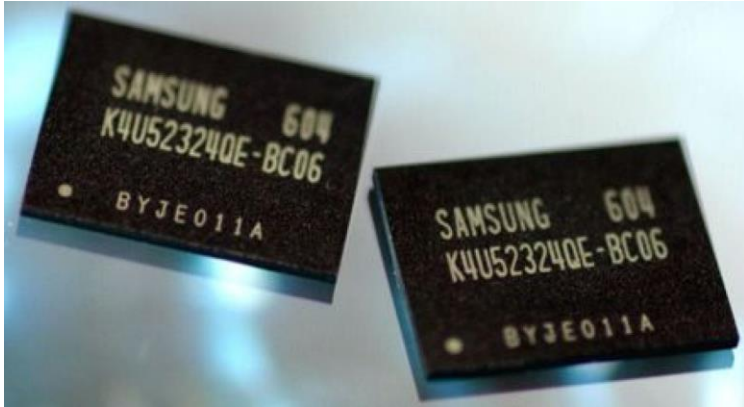
ECC Memory



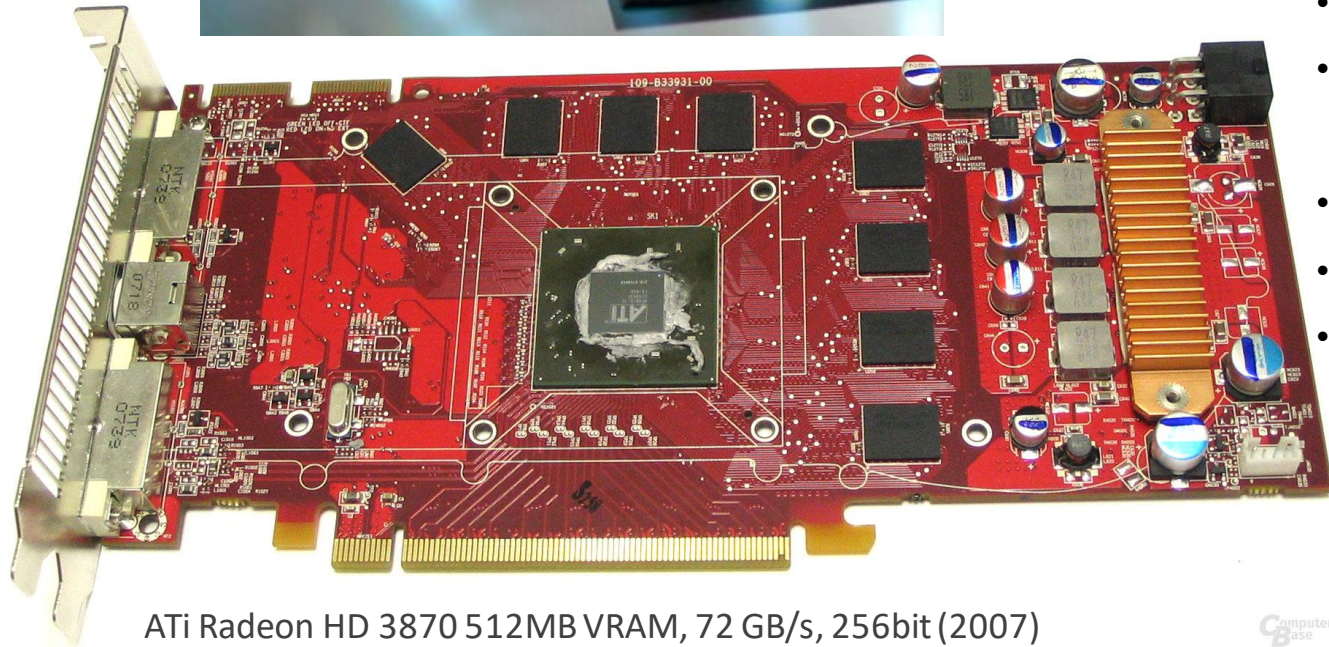
ECC DIMMs typically have 9 memory chips on each side

- Immune to 1bit errors (/64bits)
- Servers: scientific, finance, L1-L2
- Error => crash, data corr., sec.
- Row hammer: security exploit
- Electrical, magnetic interference
- Cosmic secondaries - neutrons
- 1.5km: 3.5x, 10km: 300x
- Cassini-Huygens: =112/Gb/day
- Google servers: 1.67/Gb/day
- Doesn't inc. with dec. Size
- Hamming code, Chipkill ECC (interleaved)
- Non-ECC cant correct errors

GDDR4 SDRAM

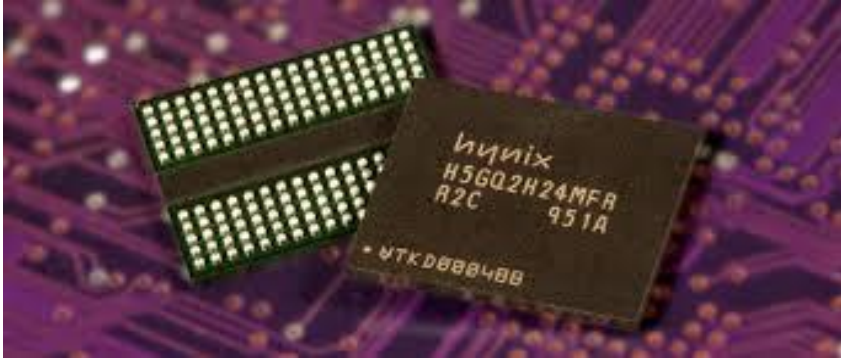


- Rival to Rambus XDR DRAM (2005)
- GDDR4: Based on DDR3, 32bit, 1.5V
- Data Bus Inversion (DBI): -PWR, -GND bounce
- $2.5 \text{ Gb/s} \times 32\text{bit} = 10 \text{ GB/s}$ (256Mb, 2005)
- $4 \text{ Gb/s} \times 32\text{bit} = 16 \text{ GB/s}$ (512Mb, 2007)
- AMD Radeon HD 3870 GDDR4: 512MB, 72 GB/s
- $1126\text{MHz mem clock} \times 2 \text{ DDR} = 2.25 \text{ Gb/s}$
- $(8 \times 512\text{Mb}) \times 2.25 \text{ Gb/s} \times 32\text{b} = 72 \text{ GB/s}, 256\text{bit}$



ATI Radeon HD 3870 512MB VRAM, 72 GB/s, 256bit (2007)

GDDR5 SDRAM

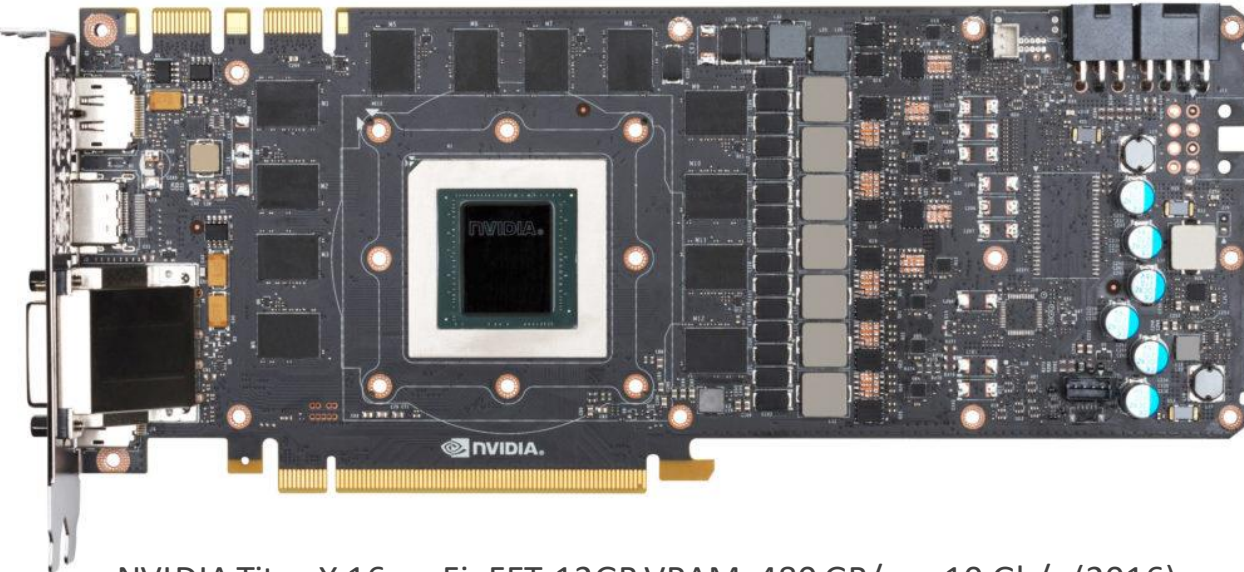


- Used in GFX, consoles, HPC (2007)
- GDDR5: Based on DDR3, 32bit, 67 signal, 170 BGA
- Command CK: 1.25GHz, Data WCK: 2.5GHz (2x)

- $32b \times 2 \text{ DDR} = 64\text{bit/WCK}$
- $32b \times 2 \text{ DDR} \times 2 \text{ WCK} \times 2 \text{ CK} = 256\text{bit (transfer)}$

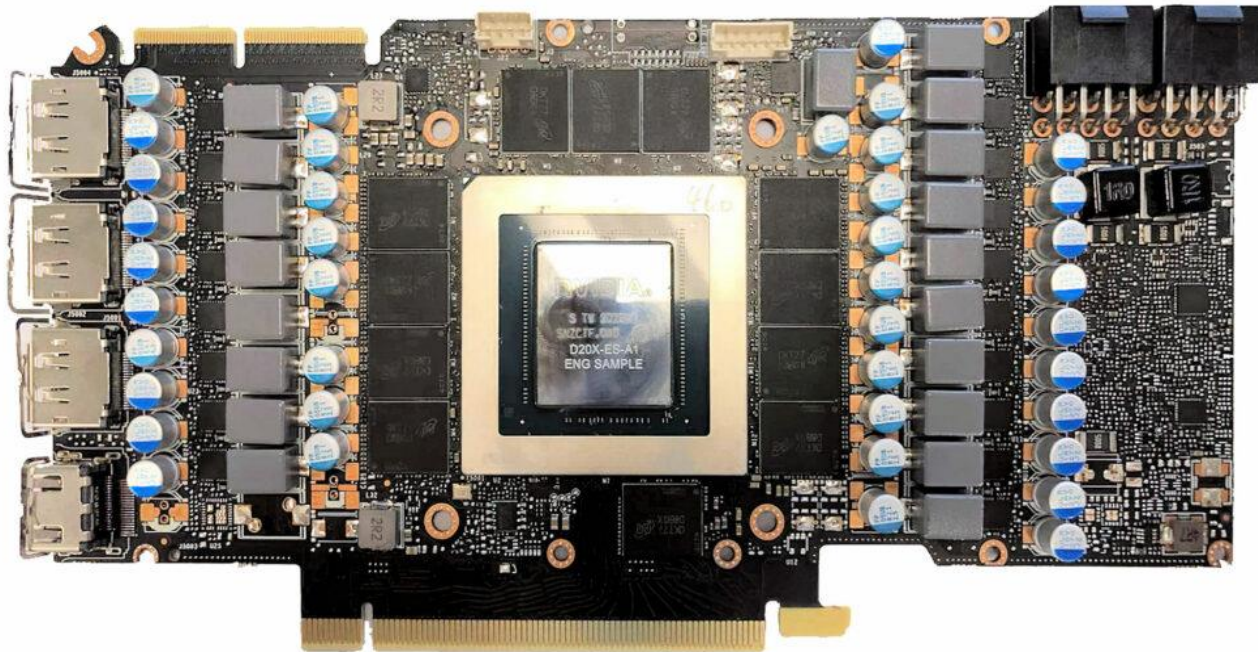
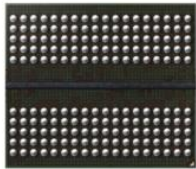
- GDDR5: 5 Gb/s \times 32bit = 20 GB/s (1Gb, 2008)
- GDDR5: 8 Gb/s \times 32bit = 32 GB/s (8Gb, 2015)
- GDDR5X: DDR / Quad Data Rate (QDR), 190 BGA
- GDDR5X: 11 Gb/s \times 32bit = 44 GB/s (2016)

- NVIDIA Titan X GDDR5X: 12GB, 480 GB/s
- $(12 \times 1\text{GB}) \times 40 \text{ GB/s} = 480 \text{ GB/s}, 384\text{bit}$



NVIDIA Titan X 16nm FinFET, 12GB VRAM, 480 GB/s or 10 Gb/s (2016)

GDDR6 SDRAM

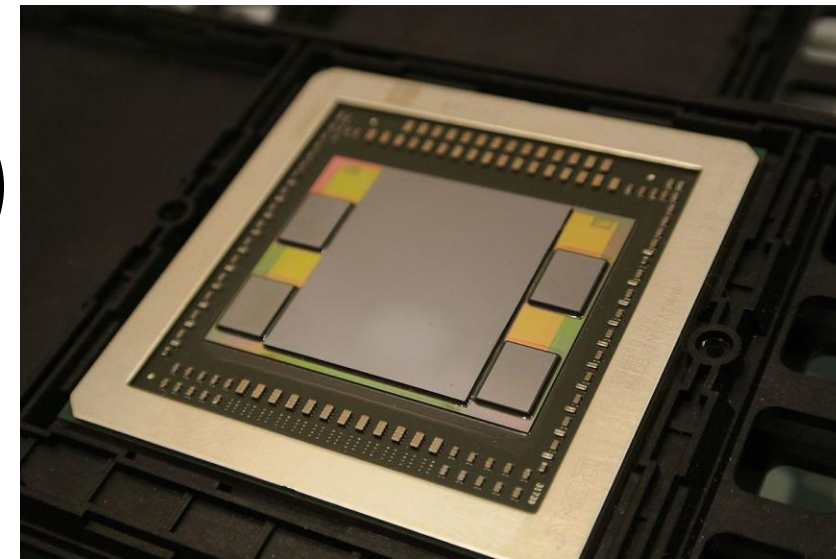


NVIDIA GeForce RTX 3090, Ampere, 24GB VRAM, 19.5 Gb/s (2016)

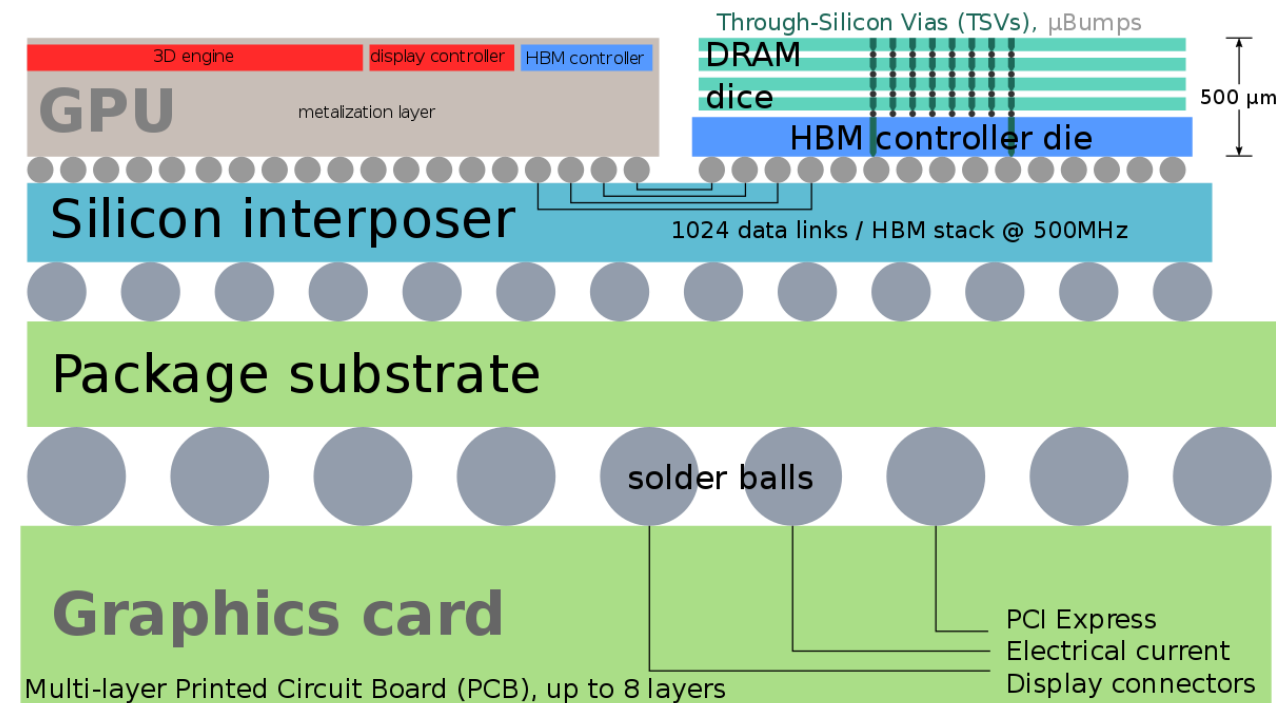
- Used in GFX, consoles, HPC (2018)
- GDDR6: $18 \text{ Gb/s} \times 32\text{bit} = 72 \text{ GB/s}$ (2GB, 2018)
- GDDR6X: $20 \text{ Gb/s} \times 32\text{bit} = 80 \text{ GB/s}$ (2020)
- GDDR6: Quad Data Rate (QDR), 1.35V
- GDDR6X: PAM4, +PHY, -SNR, +BW, -PWR/bit
- GDDR6 RAM: 12GB, 768 GB/s
- $(12 \times 1\text{GB}) \times 72 \text{ GB/s} = 768 \text{ GB/s}$, 384bit
- NVIDIA RTX 3090: 24GB, 19.5 Gb/s
- $(12 \times 2\text{GB}) \times 19.5 \text{ Gb/s} \times 32\text{b} = 936 \text{ GB/s}$, 384b

High Bandwidth Memory (HBM)

- 65nm silicon interposer, 1.3V
- Heat, engineering issues
- Costlier than PCB
- Used in high BW apps
- HBM: AMD Fiji Radeon R9 Fury X (2015)
- $128\text{bit} \times 2 \text{ channels} \times 4 \text{ dies} = 1024\text{bit}$
- $500\text{MHz} \times 2 \text{ DDR} \times 1024\text{b} = 128 \text{ GB/s}$ (4GB, 2013)
- HBM2: Nvidia Tesla P100 (2016)
- HBM2: $2 \text{ GT/s} \times 1024\text{b} = 256 \text{ GB/s}$ (8GB, 2016)
- HBM2E: $3.6 \text{ GT/s} \times 1024\text{b} = 460 \text{ GB/s}$ (16GB, 2019)
- (independent channels)

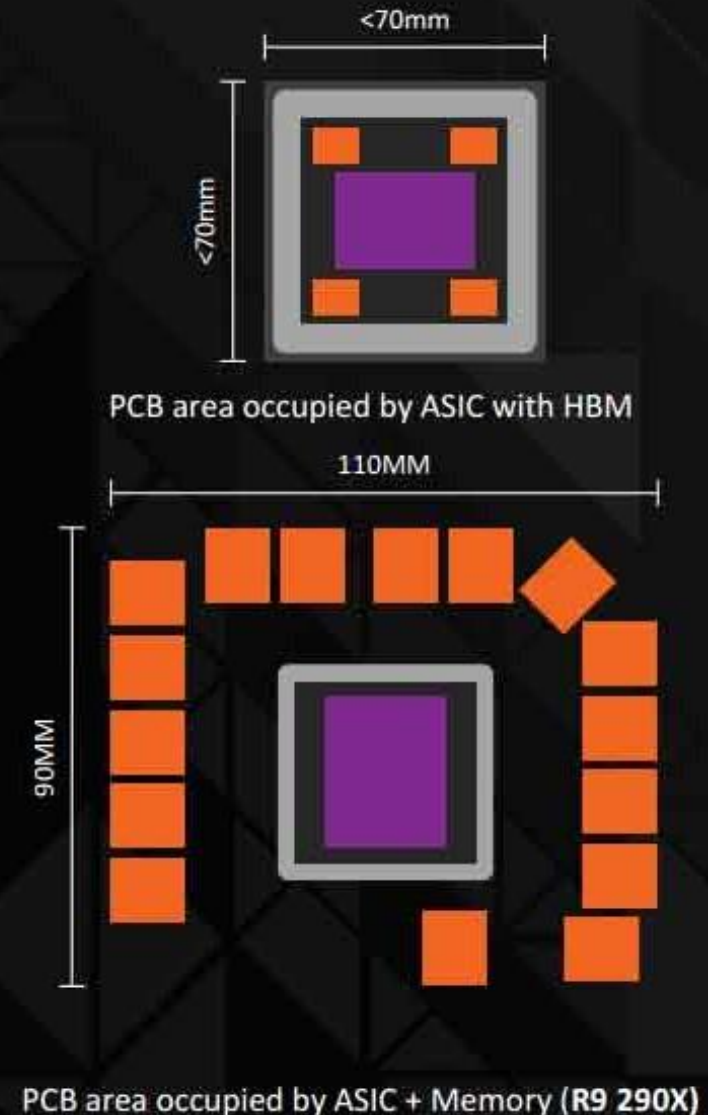
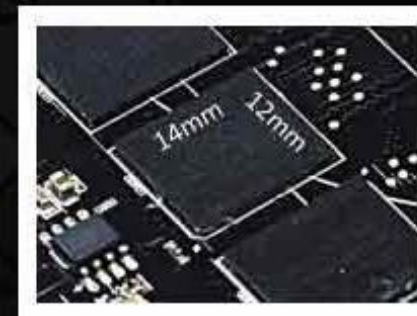
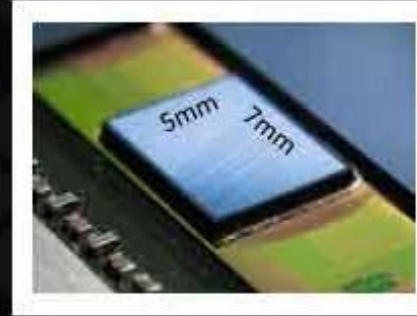


AMD Fiji, the first GPU to use HBM (2015)



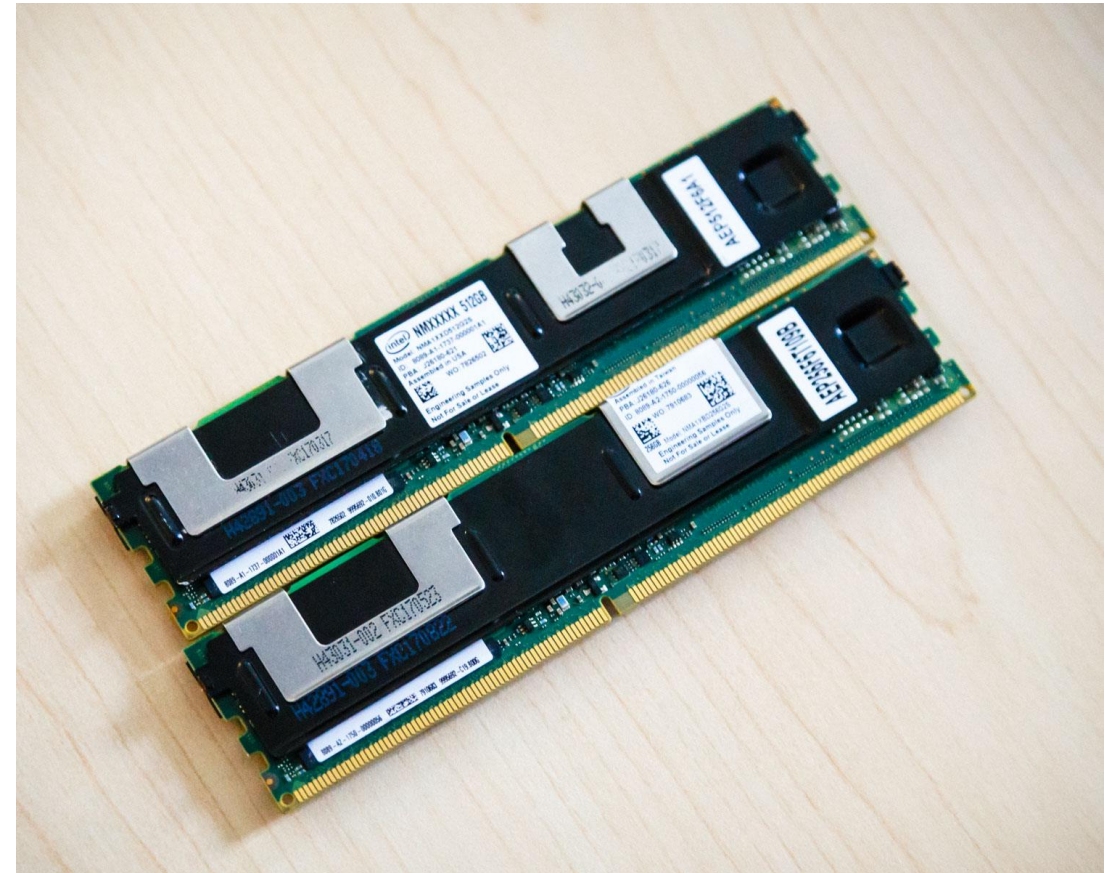
High Bandwidth Memory (HBM)

- GDDR5 chips not getting smaller
 - Large no. of chips needed for high BW
 - High PCB area needed, complex routing
 - Higher power needed due to termination
 - More signal integrity challenges
 - Larger SoC PHY area needed
-
- HBM ~3x less power requirement than GDDR5
 - 94% less chip area than GDDR5 (=capacity)
 - 50% less PCB area than GDDR5 system
 - 2.5D interposer costly, relatively new



Non-Volatile RAM (NVRAM)

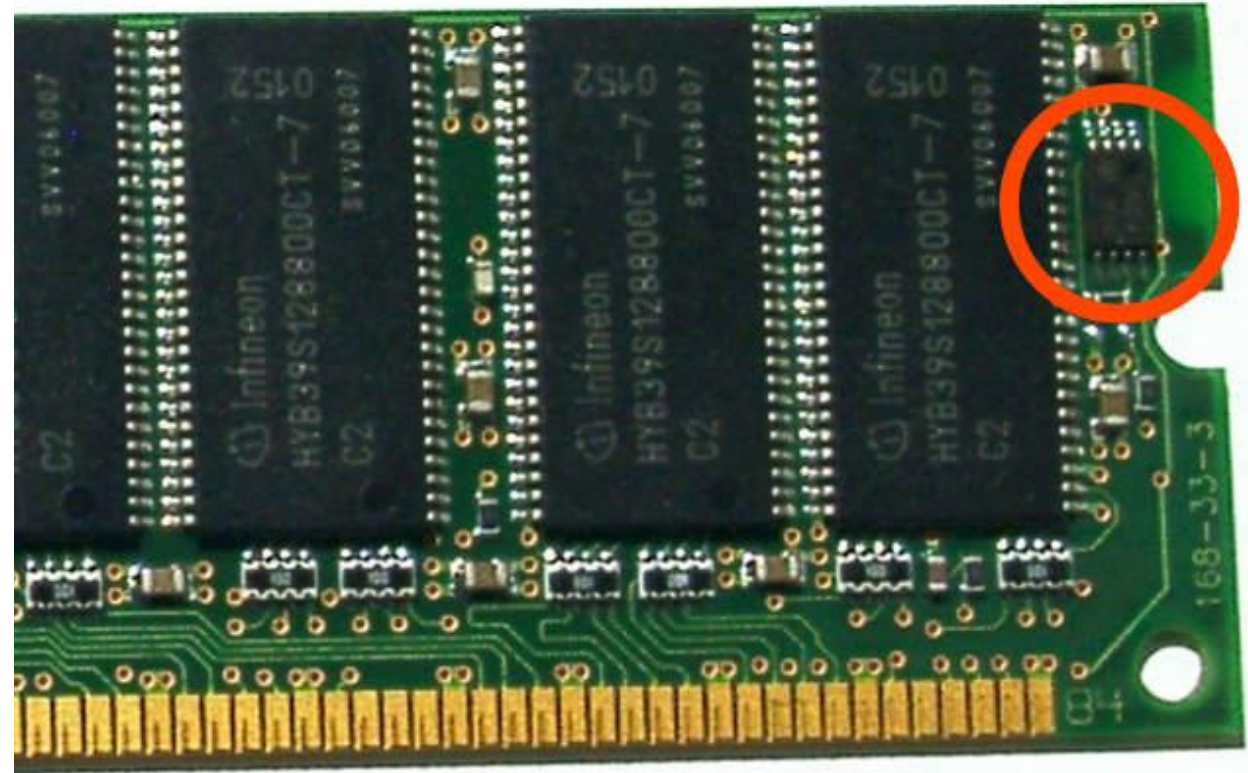
- Floating-gate MOSFET
- EPROM, EEPROM, EEPROM+SRAM, Flash
- Phase-change RAM (PCRAM): 3D XPoint Intel Optane, Micron Quantx
- Ferroelectric RAM (FeRAM)
- Magnetoresistive RAM (MRAM)
- Electrochemical RAM (ECRAM)
- Resistive RAM (ReRAM)
- Can be fully-powered down
- For in-memory analog mat-mul (DNN)



Two Intel Optane 256GB DDR4 DIMMs with AES-256 (2019)

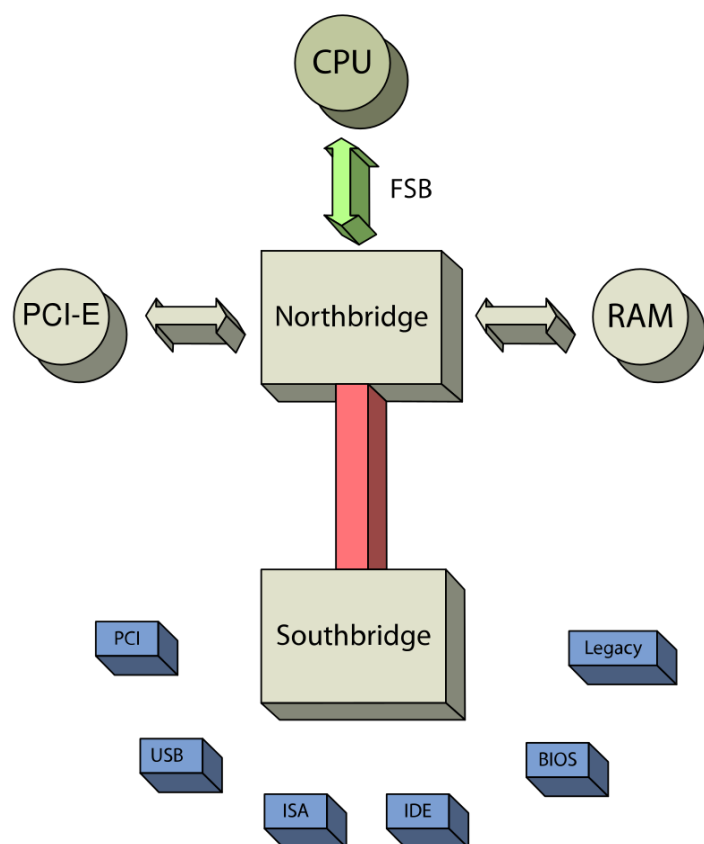
Serial Presence Detect (SPD)

- Standardized way to automatically access information about a memory module
- What memory timings to use to access the memory
- Overclocking: over-ride SPD data
- Accessed using SMBus, a variant of the I²C protocol
- SMBus: System Monitor - power supply, CPU temp., fan speeds.
- XMP uses bytes 176-255, unallocated by JEDEC, to encode higher-performance memory timings.

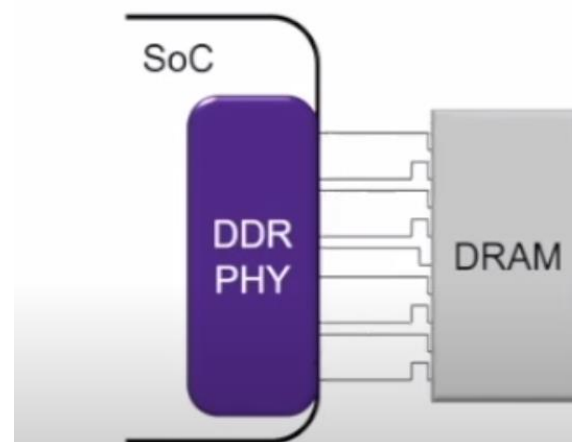


Memory device on an [SDRAM](#) module, containing SPD data

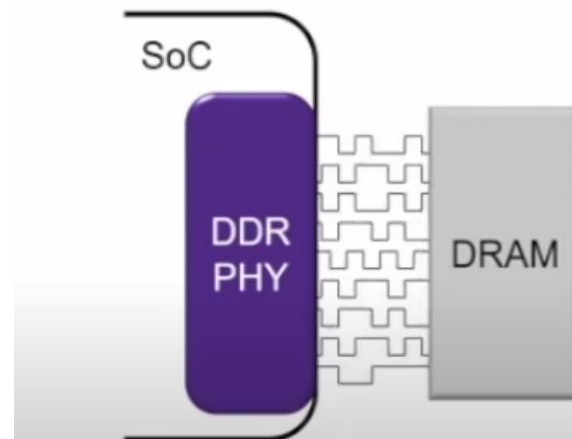
DDR PHY Training



Traditional HW Based Training



Firmware Based Training



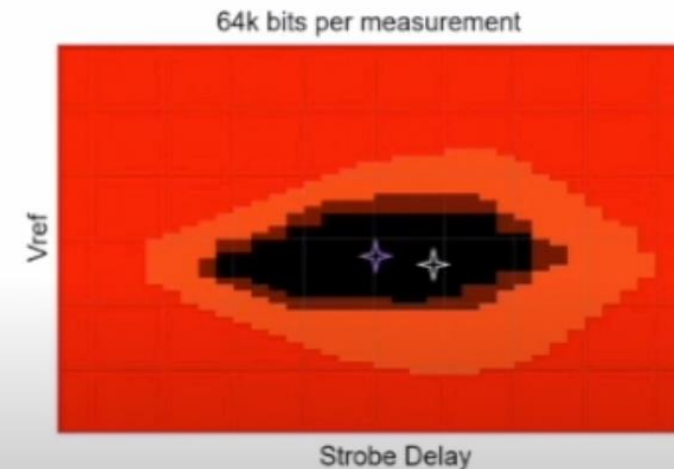
Traditional Hardware Based Training

- Typically using simple fixed pattern
- Won't exercise all conditions to worst case
- Accesses may be sparsely spaced
- Doesn't stress the interface like mission mode traffic will



Firmware Based Training

- Uses complex transaction patterns
- 64 thousand+ states
- Each lane has a different tap point in the pattern
- Allows unique non-target-bank accesses to push device di/dt
- Most realistic comparison to worst case mission mode traffic



HISTORICALLY: WE SOLVE IT BY SHRINKING AND INTEGRATING FUNCTIONS



Processor



Source: proyectoyautja.proboards.com

Multi-Media



Source: gecko54000.free.fr

Graphics



IVR



Source: Extremetech.com

1971

1989

1993

2003

2010

2013

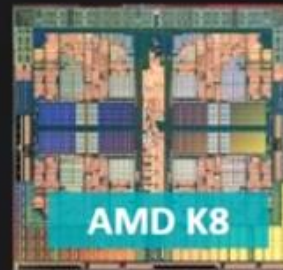
2015

Cache & FPU

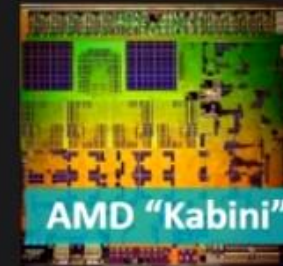


Source: gecko54000.free.fr

North Bridge



South Bridge



Source: bytesandbits.it

Die Stacking

